

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) A semiconductor device cut into respective chips by a dicing process, comprising:
 - a substrate having an edge along a dicing line;
 - a semiconductor element formed on said substrate;
 - a jetty portion formed between said semiconductor element and said edge on said substrate and having a laminated structure; and
 - an electrode pad for signal input and output which is formed on said ~~substrate-semiconductor element~~, and inside of the outermost wall of said jetty portion.
2. (Original): The semiconductor device according to claim 1, wherein said jetty portion continuously extends along said edge in parallel.
3. (Original) The semiconductor device according to claim 1, wherein said jetty portion is formed so as to surround periphery of said semiconductor element.
4. (Original) The semiconductor device according to claim 1, wherein
 - said semiconductor element includes an insulating layer and a conducting layer formed on said insulating layer;

said jetty portion includes an insulating layer and a conducting layer
formed on said insulating layer;

said insulating layer of said semiconductor element and said insulating
layer of said jetty portion are formed in the same process; and

said conducting layer of said semiconductor element and said conducting
layer of said jetty portion are formed in the same process.

5. (Currently Amended) The semiconductor device according to claim [[4]] 1,
wherein said electrode pad for signal input and output is formed on said conducting
layer of said semiconductor element, and ~~said semiconductor device further comprising~~
wherein said jetty portion includes a conducting layer and an electrode pad for said jetty
portion which is formed inside of said outermost wall on said conducting layer of the
jetty portion, and which is connected electrically to said electrode pad for signal input
and output in order to make potential difference between said conducting layer of said
jetty portion and said conducting layer of said semiconductor element close to zero.

6. (Original) A semiconductor device comprising:
a substrate;
a structure body supported by a fixing portion so as to form a space
between said substrate and said structure body; and
a jetty portion formed on said substrate between the outer periphery of
said substrate and a portion of said structure body which is not supported by said fixing
portion.

7. (Original) The semiconductor device according to claim 6, wherein a plurality of said jetty portions are formed so as to surround the outer periphery of said structure body.

8. (Original) The semiconductor device according to claim 6 further comprising an electrode pad for signal input and output which is formed on said structure body and inside of the outermost wall of said jetty portion.

9. (Original) The semiconductor device according to claim 8, wherein a plurality of said jetty portions are formed so as to surround said structure body and said electrode pad for signal input and output is arranged inside of an imaginary outer periphery which is formed by connecting the outermost walls of said jetty portions.

10. (Original) The semiconductor device according to claim 6, wherein
said structure body includes a conducting layer formed on said fixing
portion;

said jetty portion includes an insulating layer and a conducting layer
formed on said insulating layer;

said fixing portion of said structure body and said insulating layer of said
jetty portion are formed in the same process; and

said conducting layer of said structure body and said conducting layer of
said jetty portion are formed in the same process.

11. (Currently Amended) The semiconductor device according to claim 10, wherein said electrode pad for signal input and output is formed on said conducting layer of said structure body and said semiconductor device further comprising an electrode pad for said jetty portion which is formed on said conducting layer of ~~[[the]]~~ said jetty portion, and which is connected electrically to said electrode pad for signal input and output in order to make potential difference between said conducting layer of said jetty portion and said conducting layer of said structure body close to zero.

12. (Currently Amended) The semiconductor device according to claim 10 further comprising a potential ~~equalizing means~~ equalizer in order to make potential difference between said conducting layer of said jetty portion and said conducting layer of said structure body close to zero.

13. (Currently Amended) The semiconductor device according to claim ~~[[11]]~~ 8 further comprising an impedance ~~detecting means~~ detector which is connected to said electrode pad for signal input and output to detect impedance change between said structure body and said substrate.

14. (Currently Amended) The semiconductor device according to claim ~~[[1]]~~ 6, wherein an upper portion of inside area of said jetty portion is opened.

15. (New) The semiconductor device according to claim 1, wherein said jetty portion includes an insulating layer and a conducting layer which is formed on said insulating layer.

16. (New) The semiconductor device according to claim 4 further comprising a potential equalizer which makes the potential difference between said conducting layer of said jetty portion and said conducting layer of said semiconductor element close to zero.

17. (New) The semiconductor device according to claim 1 further comprising an impedance detector which is connected to said electrode pad for signal input and output and which detects change of impedance between said semiconductor element and said substrate.

18. (New) The semiconductor device according to claim 1, wherein an upper portion of inside area of said jetty portion is opened.